# TECHNICAL UNIVERISTY OF MOMBASA Faculty of Engineering \& Technology 

DEPARTMENT OF ELECTRICAL \& ELECTRONIC ENGINEERING

DIPLOMA IN ELECTRICAL ELECTRONIC ENGINEERING (DEEE 2)
EEE 2101: ANALOGUE ELECTRONICS
END OF SEMESTER EXAMINATION
SERIES: DECEMBER 2014
TIME: 2 HOURS

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## Question One (Compulsory)

a) Define the following terms as applied to atomic theory:
(i) Element
(ii) Atom
(iii) Compound marks)
b) With the aid of appropriate sketches, explain the formation of a P and N extrinsic semiconductor material
c) (i) Draw the characteristics of the P-N junction diode and explain its shape.
(ii) Explain how the diode can be used to protect the measuring instrument

## Question Two

a) Define the following terms as applied in diodes:
(i) Peak inverse voltage
(ii) Junction capacitance
(iii) Maximum operating temperature
b) With the aid of a circuit diagram, explain the operation of a bridge rectifier with a capacitive filter.
c) (I) Draw a voltage trippler circuit and outline the cycles of operation
(4 marks)
(II ) A 4.7 v Zener diode is to be used in power a stabilizing circuit. If 60 mA is required at the output and the supply voltage is 8 V , determine:
(i) The power rating of the diode
(ii) The series resistor to be connected to the circuit
(iii) The rating of the series resistor marks)

## Question Three

a) With the aid of a diagram, describe the operation of an NPN transistor
b) Use a circuit diagram to explain how biasing and stabilization is achieved in a collector biased network.
(6 marks)
c) (I) For the circuit of figure $1, \mathrm{Vce}=0, \mathrm{~V}^{\in}=\mathrm{IV}$ IC $=9.2 \mathrm{~mA}$ and ${ }^{\beta}=100$. Determine:
(i) The value of IB
(ii) The values of R1 and R2 assuming that the current through R2 is 10 x the basic current.
(II) State the function of the capacitors in the circuit

## Question Four

a) Using sketches, explain the operation of the following classes of amplifiers:

Class A
Class B
Class C
b) State any THREE comparisons between BJT and FET
c) (i) With the aid of diagrams describe the construction of an enhancement mode MOSFET.
(ii) For the circuit of figure 2 , show that $\mathrm{AV}=\mathrm{gm}$ RL stating any assumptions made. (8 marks)


## Question Five

a) Define the following terms:
(i) Sensitivity
(ii) Aquadag
(iii) Thermionic emission
b) Draw the cathode Ray Oscilloscope (CRO) block diagram and state the functions of each
(10 marks)
c) (i) Explain how a CRO can be used to measure voltages
(ii) Determine the value of the unknown frequency for figure 3 if the known frequency is 15 KHZ (7 marks)
Figure 3


[^0]:    Instructions to Candidates:
    You should have the following for this examination

    - Answer Booklet

    This paper consists of FIVE questions. Answer any THREE questions
    Maximum marks for each part of a question are as shown

